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FDP52N20 / FDPF52N20T N-Channel UniFETTM MOSFET 200 V, 52 A, (- mΩ

Features

- R $_{DS(on)}$ = 41 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 26 A
- Low Gate Charge (Typ. 49 nC)
- Low C_{RSS} (Typ. 66 pF)
- 100% Avalanche Tested
- RoHS Compliant

Applications

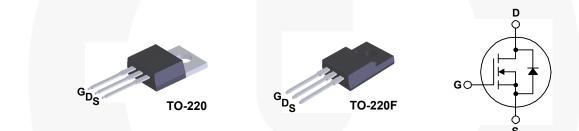
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

December 2013

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Description

UniFET[™] MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

			FDP52N20	FDPF52N20T	Unit
Drain to Source Voltage		200		V	
Gate to Source Voltage		±30		V	
DrainCurrent	- Continuous (T _C = 25°C)		52	52*	^
	- Continuous (T _C = 100 ^o C)		33	33*	A
Drain Current	- Pulsed	(Note 1)	208	208*	Α
Single Pulsed Avalanche Energy (Note 2)		2520		mJ	
Avalanche Current		(Note 1)	52		А
Repetitive Avalanche Energy		(Note 1)	35.7		mJ
Peak Diode Recovery dv/dt (Not		(Note 3)	4.5		V/ns
Dewer Dissinction	$(T_{C} = 25^{\circ}C)$		357	38.5	W
Power Dissipation	- Derate above 25°C		2.86	0.3	W/ºC
Operating and Storage Temperature Range		-55 to +150		°C	
•	0		3	00	°C
	Drain Current Drain Current Single Pulsed Avalanche Energy Avalanche Current Repetitive Avalanche Energy Peak Diode Recovery dv/dt Power Dissipation Operating and Storage Temp Maximum Lead Temperature 1/8" from Case for 5 Seconds	$\begin{tabular}{ c c c c }\hline \hline Drain Current & - Continuous (T_C = 25^\circ C) \\ \hline - Continuous (T_C = 100^\circ C) \\ \hline Drain Current & - Pulsed \\ \hline Single Pulsed Avalanche Energy \\ \hline Avalanche Current & \\ \hline Repetitive Avalanche Energy \\ \hline Peak Diode Recovery dv/dt \\ \hline Power Dissipation & \hline (T_C = 25^\circ C) \\ \hline - Derate above 25^\circ C \\ \hline \end{tabular}$	$ \begin{array}{c} - \operatorname{Continuous}\left(T_{C} = 25^{\circ} C \right) \\ \hline - \operatorname{Continuous}\left(T_{C} = 100^{\circ} C \right) \\ \hline - \operatorname{Continuous}\left(T_{C} = 100^{\circ} C \right) \\ \hline - \operatorname{Continuous}\left(T_{C} = 100^{\circ} C \right) \\ \hline - \operatorname{Continuous}\left(T_{C} = 100^{\circ} C \right) \\ \hline - \operatorname{Pulsed} & (\operatorname{Note} 1) \\ \hline \operatorname{Single Pulsed Avalanche Energy} & (\operatorname{Note} 2) \\ \hline \operatorname{Avalanche Current} & (\operatorname{Note} 1) \\ \hline \operatorname{Repetitive Avalanche Energy} & (\operatorname{Note} 1) \\ \hline \operatorname{Repetitive Avalanche Energy} & (\operatorname{Note} 1) \\ \hline \operatorname{Repetitive Avalanche Energy} & (\operatorname{Note} 3) \\ \hline \operatorname{Power Dissipation} & \\ \hline \begin{array}{c} (T_{C} = 25^{\circ} C) \\ - \operatorname{Derate above} 25^{\circ} C \\ \hline \\ - \operatorname{Derate above} 25^{\circ} C \\ \hline \\ \end{array} \\ \hline \end{array} \\ \hline \begin{array}{c} \operatorname{Maximum Lead Temperature for Soldering, \\ 1/8'' from Case for 5 Seconds \\ \hline \end{array} $	$\begin{array}{c c c c c c c c } \hline & - Continuous (T_C = 25^\circ C) & 52 & 52 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & 33 & - Continuous (T_C = 100^\circ C) & - Continuous (T_C = 100^\circ C) & - Continuous (T_C = 20^\circ C) & - Continuous (T_C = 25^\circ C) & - Continue (T_C = 25^\circ C) & - Continue (T_C = 25^\circ C$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Thermal Characteristics

Symbol	Parameter	FDP52N20	FDPF52N20T	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.35	3.3 °C/W		
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	2.5	

FDP52N20 / FDPF52N20T — N-Channel UniFETTM MOSFET

Part Nu	mber	Top Mark	Package	Packing Method	Reel Size	Ta	ape Width	Qua	antity
FDP52N20 FDP52N20 TO		TO-220					50	50 units	
		TO-220F			N/A		50 units		
	I Chara	Acteristics $T_{\rm C} = 25^{\circ}$	C unless oth						
Symbol		Parameter		Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	cteristics	i							
BV _{DSS}	Drain to Source Breakdown Voltage		e I _D	$I_{D} = 250 \ \mu A, V_{GS} = 0 \ V, T_{J} = 25^{\circ}C$		200	-	-	V
ΔΒV _{DSS} /ΔΤ _J	Breakdown Voltage Temperature Coefficient		I _D	$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.2	-	V/ºC
	DSS Zero Gate Voltage Drain Current		VD	$V_{DS} = 200 V, V_{GS} = 0 V$		-	-	1	μA
'DSS				_S = 160 V, T _C = 125 ^o C		-	-	10	μι
I _{GSS}	Gate to E	Body Leakage Current	VG	$s_{S} = \pm 30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		-	-	±100	nA
On Charac	teristics								
V _{GS(th)}	Gate Th	reshold Voltage	VG	_{SS} = V _{DS} , I _D = 250μ A		3.0	-	5.0	V
R _{DS(on)}	Static Dr	Static Drain to Source On Resistance		V _{GS} = 10 V, I _D = 26 A		-	0.041	0.049	Ω
9 _{FS}	Forward Transconductance		VC	V _{DS} = 40 V, I _D = 26 A		-	35	-	S
Dynamic C	haracte	ristics							
C _{iss}	-	pacitance		05.14.14		-	2230	2900	pF
C _{oss}	Output C	Output Capacitance		──V _{DS} = 25 V, V _{GS} = 0 V f = 1 MHz		-	540	700	pF
C _{rss}	Reverse	Transfer Capacitance				-	66	100	pF
Q _{g(tot)}	Total Gat	te Charge at 10V				-	49	63	nC
	Gate to Source Gate Charge		Vr	$V_{DS} = 160 \text{ V}, \text{ I}_{D} = 52 \text{ A}$		-	19	-	nC
Q _{gs}		0		$V_{GS} = 10 V$ (Note 4)				-	nC
Q _{gs} Q _{gd}		Drain "Miller" Charge		_{SS} = 10 V	(Note 4)	-	24		
Q _{gd}	Gate to [Drain "Miller" Charge		_{9S} = 10 V	(Note 4)	•	24		Į
Q _{gd} Switching	Gate to I	Drain "Miller" Charge		_{3S} = 10 V	(Note 4)	-		115	ns
Q _{gd} Switching	Gate to I Characte Turn-On	Drain "Miller" Charge		_{3S} = 10 V _{DD} = 100 V, I _D = 20 A	(Note 4)		24 53 175	115 359	ns
Q_{gd} Switching $t_{d(on)}$ t_r	Gate to I Characte Turn-On Turn-On	Drain "Miller" Charge eristics Delay Time		-	(Note 4)	•	53		
Q _{gd} Switching	Gate to I Charact Turn-On Turn-On Turn-Off	Drain "Miller" Charge eristics Delay Time Rise Time		_{DD} = 100 V, I _D = 20 A	(Note 4)		53 175	359	ns
Qgd Switching t _{d(on)} t _r t _{d(off)} t _f	Gate to I Characte Turn-On Turn-On Turn-Off Turn-Off	Drain "Miller" Charge eristics Delay Time Rise Time Delay Time Fall Time		_{DD} = 100 V, I _D = 20 A	-		53 175 48	359 107	ns ns
Q _{gd} Switching t _{d(on)} t _r t _{d(off)} t _f Drain-Sou	Gate to I Characte Turn-On Turn-Off Turn-Off Turn-Off	Drain "Miller" Charge eristics Delay Time Rise Time Delay Time		$I_{D} = 100 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ $I_{3} = 25 \Omega$	-		53 175 48	359 107	ns ns
Q _{gd} Switching t _{d(on)} t _r t _{d(off)} t _f Drain-Sou	Gate to I Characte Turn-On Turn-Off Turn-Off Turn-Off Turn-Off Ce Diod	Drain "Miller" Charge eristics Delay Time Rise Time Delay Time Fall Time e Characteristics		$P_D = 100 \text{ V}, \text{ I}_D = 20 \text{ A}$ $P_S = 25 \Omega$	-		53 175 48 29	359 107 68	ns ns ns
Q _{gd} Switching t _{d(on)} t _r t _{d(off)} t _f	Gate to I Characte Turn-On Turn-Off Turn-Off rce Diod Maximum Maximum	Drain "Miller" Charge eristics Delay Time Rise Time Delay Time Fall Time e Characteristics n Continuous Drain to Sou	V _G V _D R _G rce Diode Fo	$P_D = 100 \text{ V}, \text{ I}_D = 20 \text{ A}$ $P_S = 25 \Omega$	-		53 175 48 29 -	359 107 68 52	ns ns ns A
Q _{gd} Switching t _{d(on)} t _r t _{d(off)} t _f Drain-Sou I _S I _{SM}	Gate to I Characte Turn-On Turn-On Turn-Off Turn-Off rce Diod Maximun Maximun Drain to S	Drain "Miller" Charge eristics Delay Time Rise Time Delay Time Fall Time e Characteristics n Continuous Drain to Sou n Pulsed Drain to Source I	V _G V _D V _D R _G Prce Diode For Diode Forwar tage V _G	$I_D = 100 \text{ V}, I_D = 20 \text{ A}$ $I_S = 25 \Omega$ rward Current d Current	-	· · · ·	53 175 48 29 - -	359 107 68 52 204	ns ns ns A

Notes:

1: Repetitive rating: pulse-width limited by maximum junction temperature. 2: L = 1.4 mH, $I_{AS} = 52 \text{ A}$, $V_{DD} = 50 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}\text{C}$. 3: $I_{SD} \le 52 \text{ A}$, di/dt $\le 200 \text{ A/}\mu\text{s}$, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}\text{C}$.

4: Essentially independent of operating temperature typical characteristics.



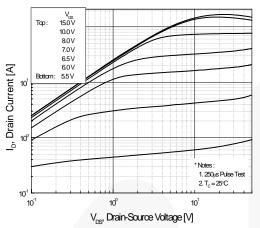


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

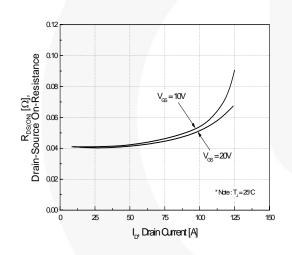


Figure 5. Capacitance Characteristics

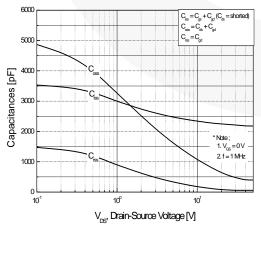


Figure 2. Transfer Characteristics

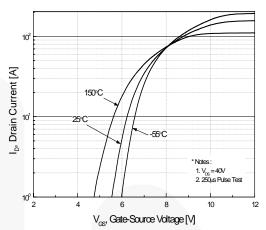


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

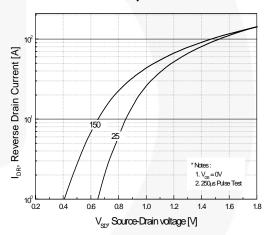
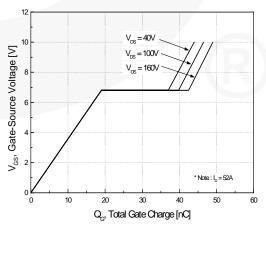
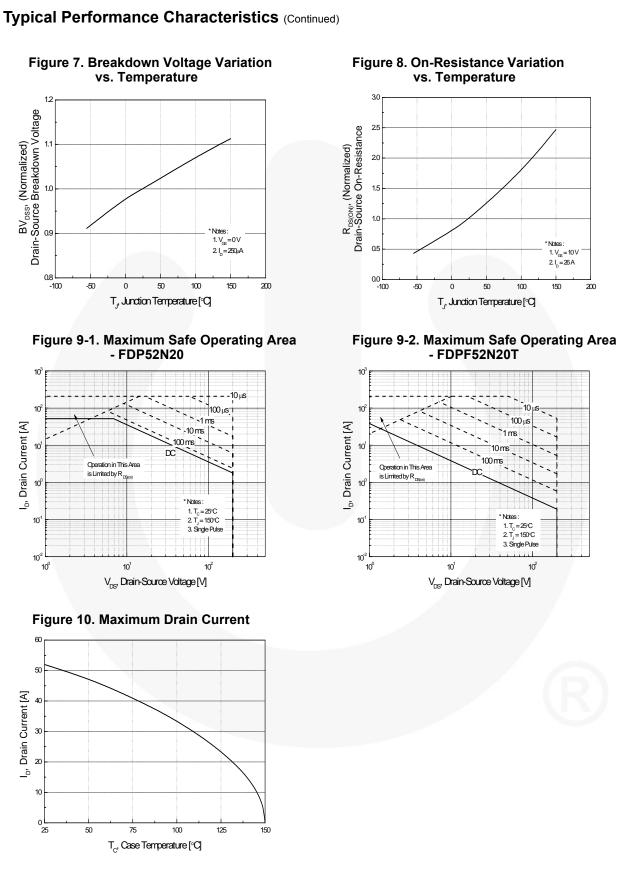


Figure 6. Gate Charge Characteristics



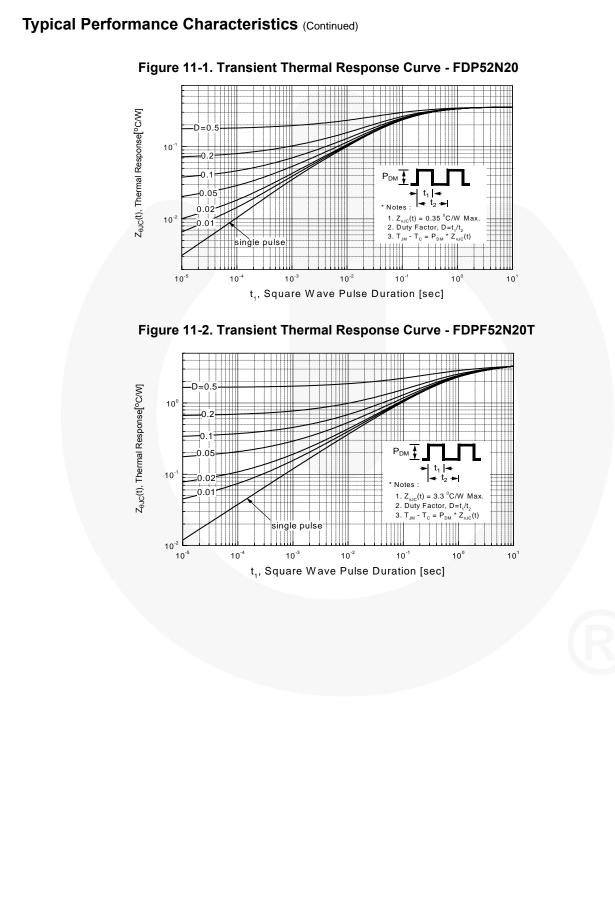


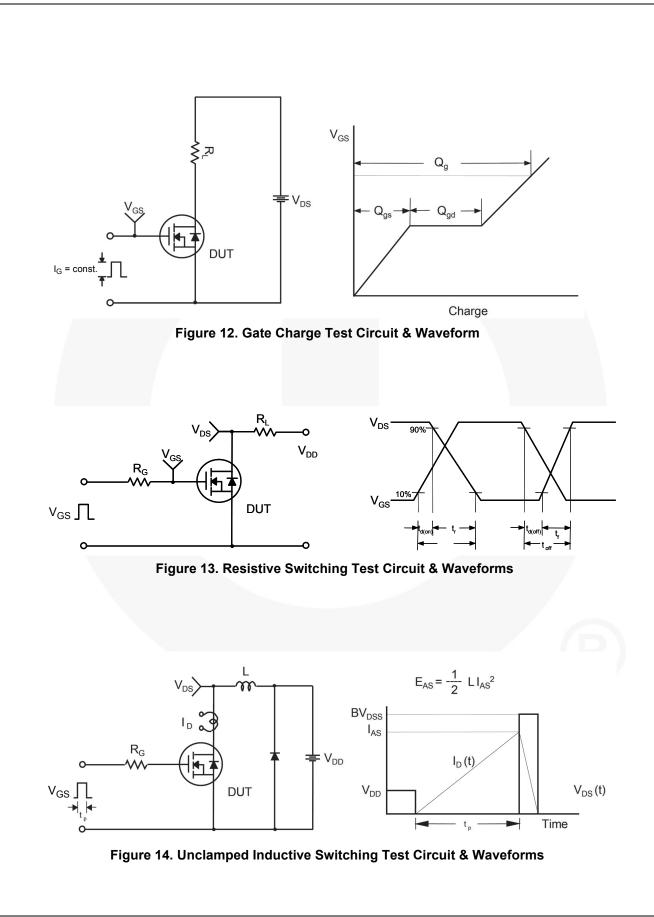
I_D, Drain Current [A]

Drain Current [A]

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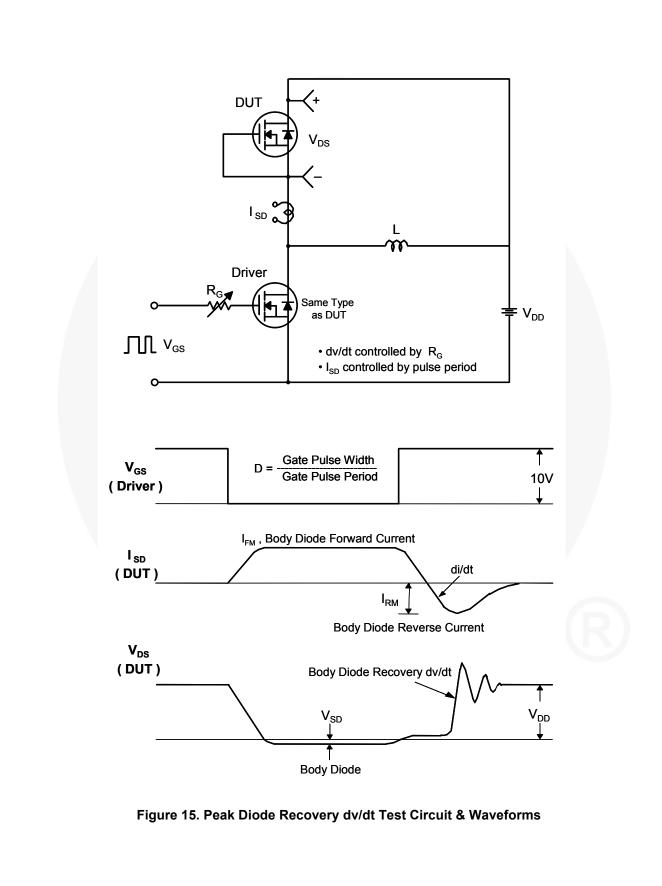
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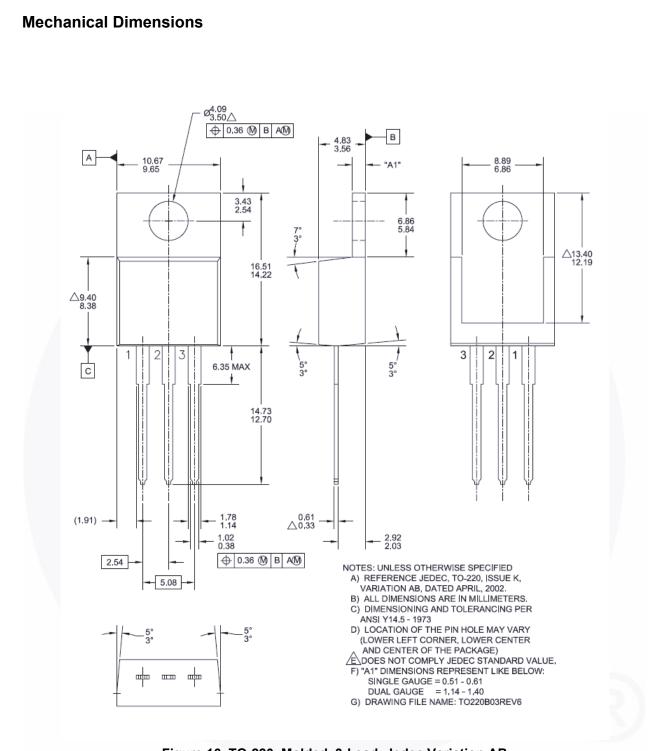
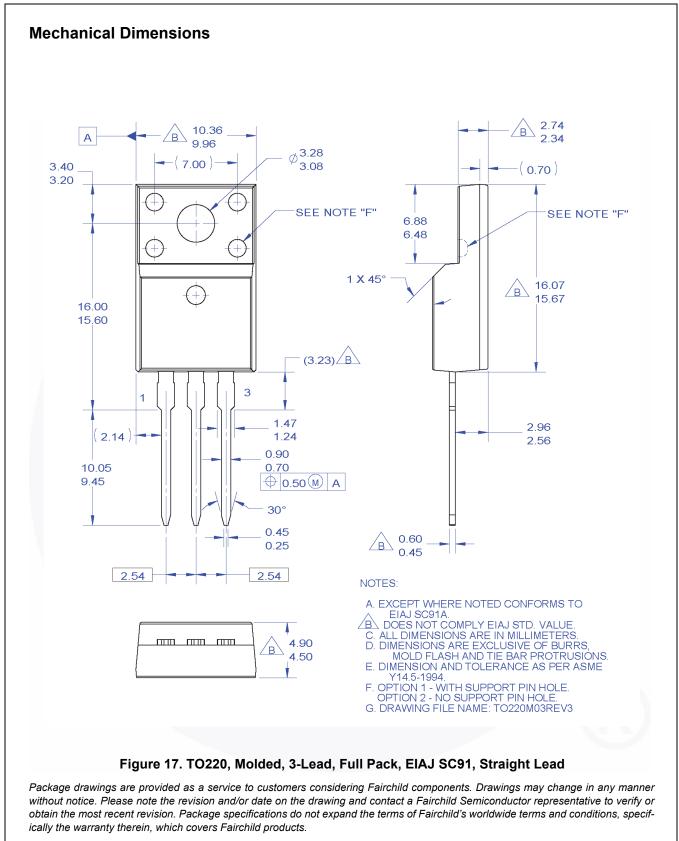


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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